

TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP331,TLP332

Office Machine
Household Use Equipment
Programmable Controllers
AC / DC-Input Module
Telecommunication

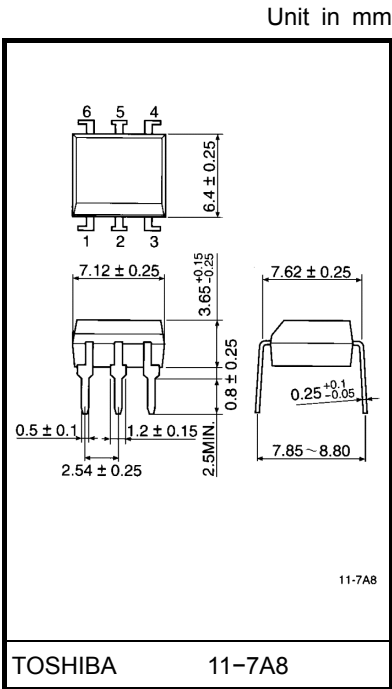
The TOSHIBA TLP331 and TLP332 consists of a gallium arsenide infrared emitting diode optically coupled to a photo-transistor in a six lead plastic DIP package.
This photocoupler provides the unique feature of high current transfer ratio at both low output voltage and low input current. This makes it ideal for use in low power logic circuits, telecommunications equipment and portable electronics isolation applications.
TLP332 is no-base internal connection for high-EMI environments.

- Collector-emitter voltage: 55V (min.)
- Isolation voltage: 5000Vrms (min.)
- UL recognized: UL1577, file no. E67349
- Current transfer ratio

Classi- fication (*)	Current Transfer Ratio (min.)			Marking Of Classi- fication
	Ta = 25°C		Ta = -25~75°C	
	IF = 1mA VCE = 0.5V	IF = 0.5mA VCE = 1.5V	IF = 1mA VCE = 0.5V	
Rank BV	200%	100%	100%	BV
Standard	100%	50%	50%	BV, blank

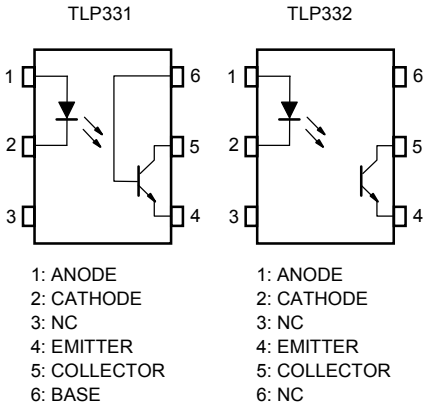
(*) Ex. Standard: TLP331
Rank BV: TLP331(BV)

(Note) Application type name for certification test,
please use standard product type name, i.e.
TLP331(BV): TLP331



Weight: 0.4 g

Pin Configurations (top view)



Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	I_F	50	mA
	Forward current derating (Ta ≥ 39°C)	$\Delta I_F / ^\circ\text{C}$	-0.7	mA / °C
	Peak forward current (100μs pulse, 100pps)	I_{FP}	1	A
	Reverse Voltage	V_R	5	V
	Junction temperature	T_j	125	°C
Detector	Collector-emitter voltage	V_{CEO}	55	V
	Collector-base voltage (TLP331)	V_{CBO}	80	V
	Emitter-collector voltage	V_{ECO}	7	V
	Emitter-base voltage (TLP331)	V_{EBO}	7	V
	Collector current	I_C	50	mA
	Power dissipation	P_C	150	mW
	Power dissipation derating (Ta ≥ 25°C)	$\Delta P_C / ^\circ\text{C}$	-1.5	mW / °C
	Junction temperature	T_j	125	°C
Storage temperature range		T_{stg}	-55~125	°C
Operating temperature range		T_{opr}	-55~100	°C
Lead soldering temperature (10s)		T_{sol}	260	°C
Total package power dissipation		P_T	250	mW
Total package power dissipation derating (Ta ≥ 25°C)		$P_T / ^\circ\text{C}$	-2.5	mW / °C
Isolation voltage (AC, 1min., RH ≤ 60%) (Note 1)		BV_S	5000	V _{rms}

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4, 5 and 6 shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	—	5	25	V
Forward current	I_F	—	1.6	25	mA
Collector current	I_C	—	1	10	mA
Operating temperature	T_{opr}	-25	—	75	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	30	—	pF
Detector	Collector–emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	55	—	—	V
	Emitter–collector breakdown voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector–base breakdown voltage (TLP331)	$V_{(BR)CBO}$	$I_C = 0.1\text{mA}$	80	—	—	V
	Emitter–base breakdown voltage (TLP331)	$V_{(BR)EBO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector dark current	I_{CEO}	$V_{CE} = 24\text{V}$	—	10	100	nA
			$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$	—	2	50	μA
	Collector dark current (TLP331)	I_{CER}	$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$ $R_{BE} = 1\text{M}\Omega$	—	0.5	10	μA
	Collector dark current (TLP331)	I_{CBO}	$V_{CB} = 10\text{V}$	—	0.1	—	nA
	DC forward current gain (TLP331)	h_{FE}	$V_{CE} = 5\text{V}, I_C = 0.5\text{mA}$	—	1000	—	—
	Capacitance (collector to emitter)	C_{CE}	$V = 0, f = 1\text{MHz}$	—	12	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I_C / I_F	$I_F = 1\text{mA}, V_{CE} = 0.5\text{V}$ Rank BV	100	—	1200	%
			200	—	1200	
Low input CTR	$I_C / I_{F(\text{low})}$	$I_F = 0.5\text{mA}, V_{CE} = 1.5\text{V}$ Rank BV	50	—	—	%
			100	—	—	
Base photo-current (TLP331)	I_{PB}	$I_F = 1\text{mA}, V_{CB} = 5\text{V}$	—	10	—	μA
Collector–emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 0.5\text{mA}, I_F = 1\text{mA}$	—	—	0.4	V
		$I_C = 1\text{mA}, I_F = 1\text{mA}$ Rank BV	—	0.2	—	
			—	—	0.4	

Coupled Electrical Characteristics (Ta = 25~75°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I_C / I_F	$I_F = 1\text{mA}, V_{CE} = 0.5\text{V}$ Rank BV	50	—	—	%
			100	—	—	
Low input CTR	$I_C / I_{F(\text{low})}$	$I_F = 0.5\text{mA}, V_{CE} = 1.5\text{V}$ Rank BV	—	50	—	%
			—	100	—	

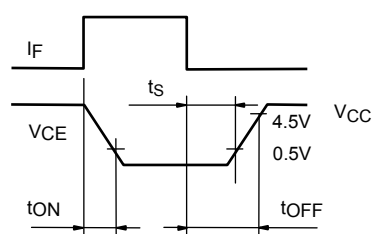
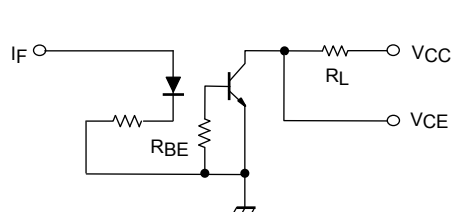
Isolation Characteristics (Ta = 25°C)

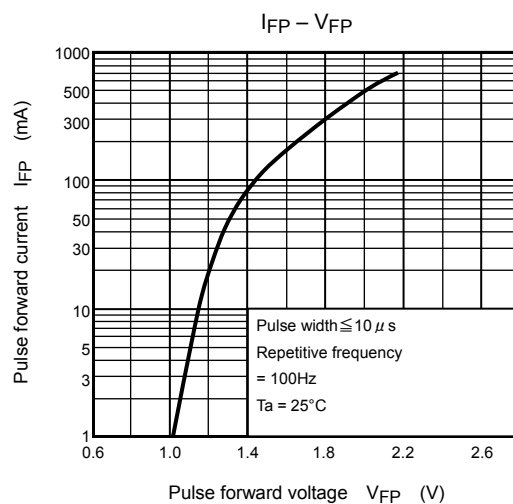
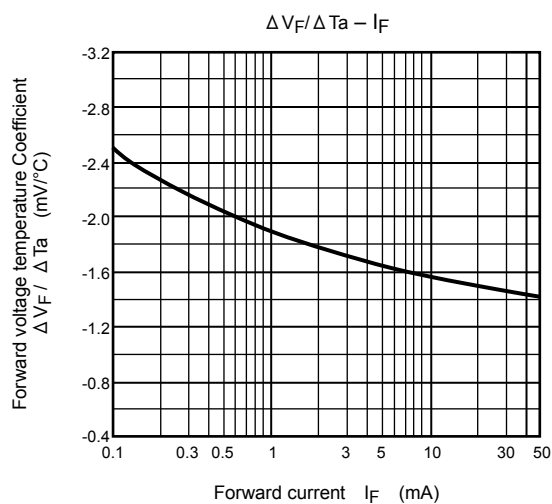
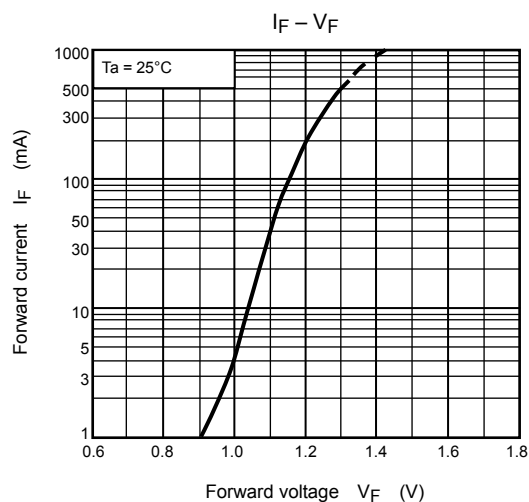
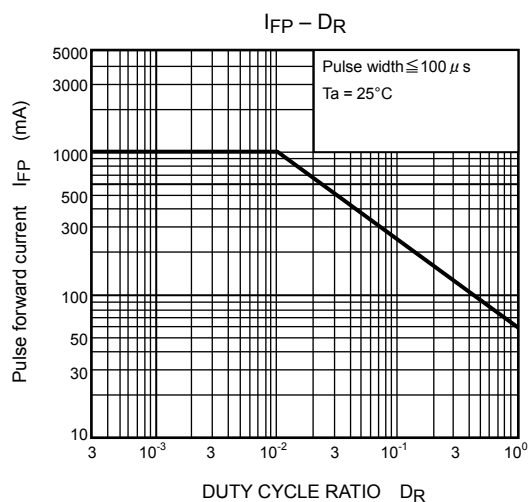
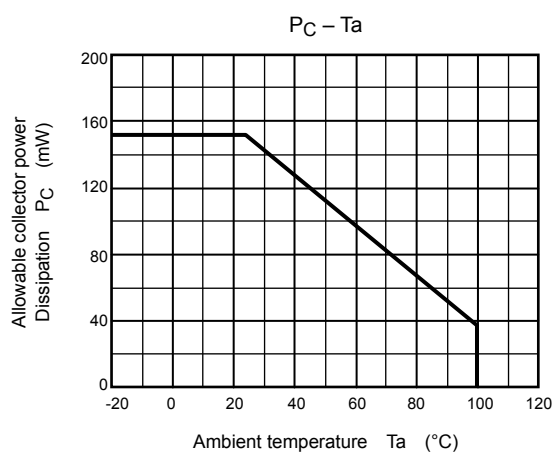
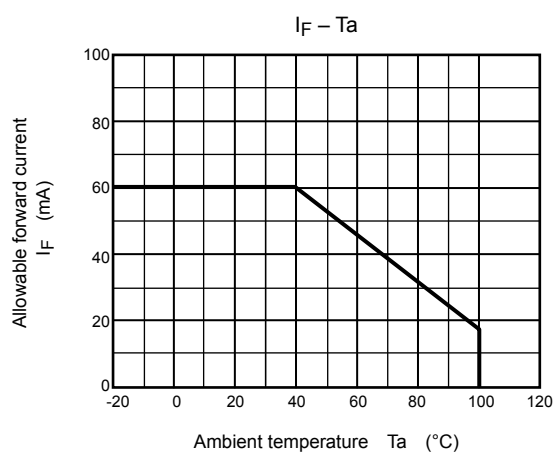
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance (input to output)	C _S	V _S = 0, f = 1MHz	—	0.8	—	pF
Isolation resistance	R _S	V = 500V	5×10 ¹⁰	10 ¹⁴	—	Ω
Isolation voltage	BV _S	AC, 1 minute	5000	—	—	V _{rms}
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V _{dc}

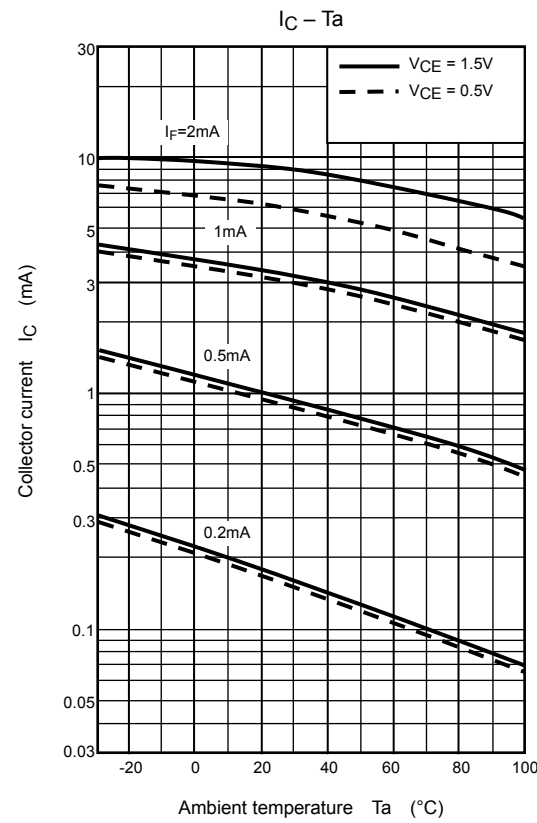
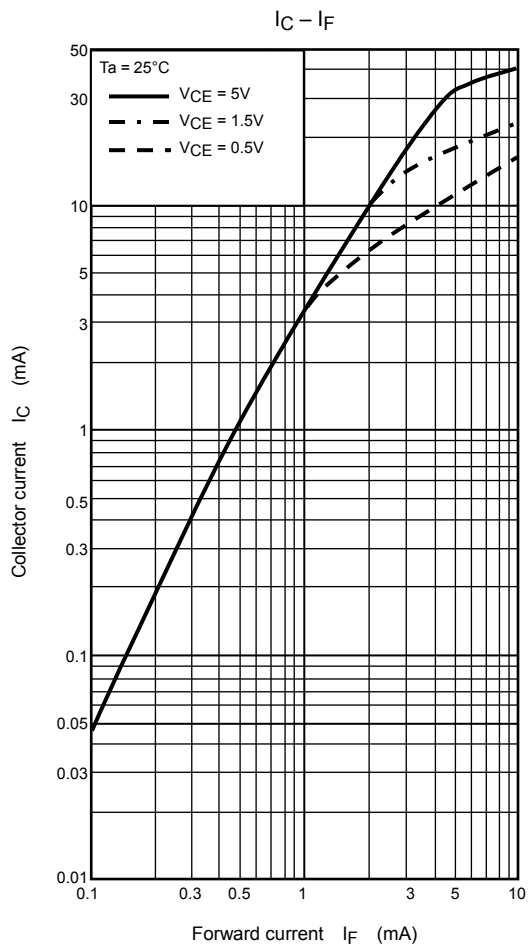
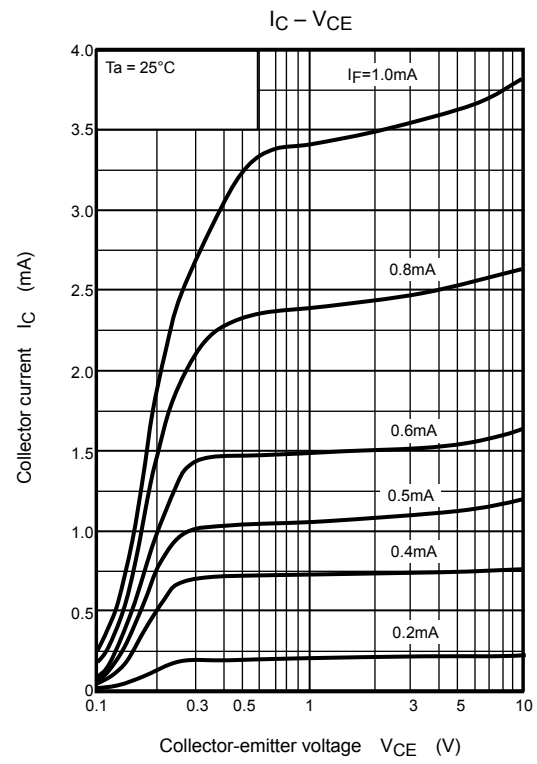
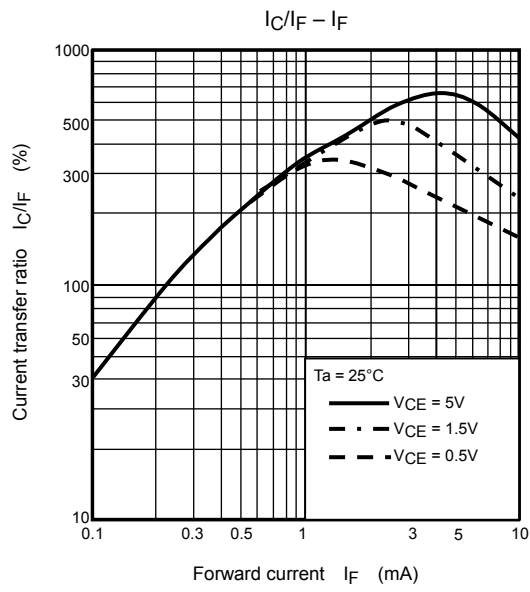
Switching Characteristics (Ta = 25°C)

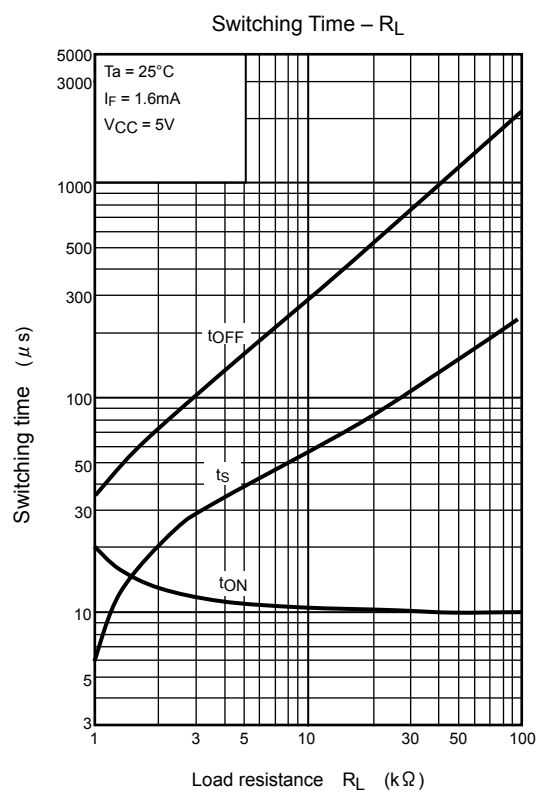
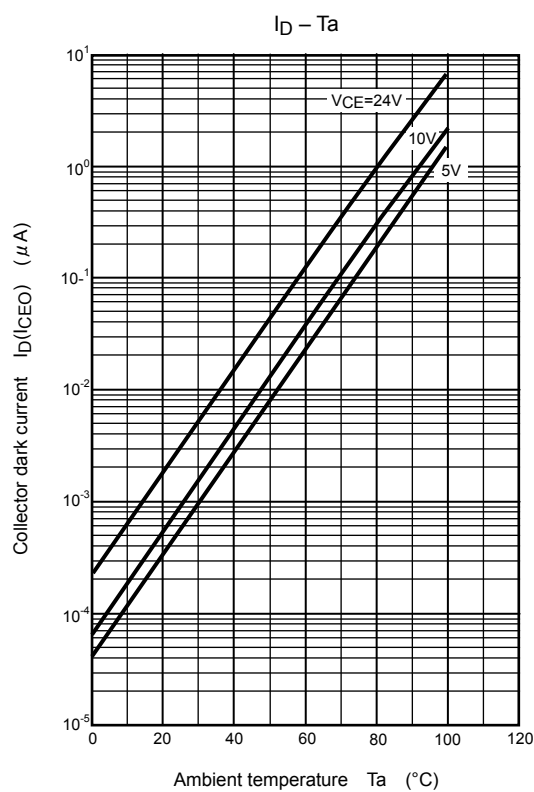
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t _r	V _{CC} = 10V I _C = 2mA R _L = 100Ω	—	8	—	μs
Fall time	t _f		—	8	—	
Turn-on time	t _{on}		—	10	—	
Turn-off time	t _{off}		—	8	—	
Turn-on time	t _{ON}	R _L = 4.7kΩ (Fig.1) R _{BE} = OPEN V _{CC} = 5V, I _F = 1.6mA	—	10	—	μs
Storage time	t _S		—	50	—	
Turn-off time	t _{OFF}		—	300	—	
Turn-on time	t _{ON}	R _L = 4.7kΩ (Fig.1) R _{BE} = 470kΩ (TLP331) V _{CC} = 5V, I _F = 1.6mA	—	12	—	μs
Storage time	t _S		—	30	—	
Turn-off time	t _{OFF}		—	100	—	

Fig. 1 Switching time test circuit









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